

### General Description

The WST2002 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST2002 meet the RoHS and Green Product requirement with full function reliability approved.

### Features

- High-speed switching
- Green Device Available
- ESD Protected:2KV

### Product Summary

BVDSS	RDSON	ID
30V	7.5Ω	600mA

### Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC
- Networking DC-DC Power System
- Load Switch

### SOT-723 Pin Configuration

### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	600	mA
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	550	mA
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	0.8	A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	0.15	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	---	625	°C/W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =10uA	30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25 °C, I <sub>D</sub> =1mA	---	0.05	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A	---	---	7.5	Ω
		V <sub>GS</sub> =5V, I <sub>D</sub> =0.05A	---	---	7.5	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1	1.85	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-3.7	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, T <sub>J</sub> =25 °C	---	---	1	uA
		V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, T <sub>J</sub> =55 °C	---	---	3	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±10	uA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =0.1A	---	80	---	mS
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =30V, V <sub>GS</sub> =10V, R <sub>G</sub> =10Ω, I <sub>D</sub> =0.2A RL=150Ω	---	12	20	ns
T <sub>d(off)</sub>	Turn-Off Delay Time		---	20	30	
C <sub>iss</sub>	Input Capacitance		---	25	50	
C <sub>oss</sub>	Output Capacitance		V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz	---	10	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	3.0	5.0	pF

\* P<sub>w</sub>≤300μs, Duty cycle≤1%

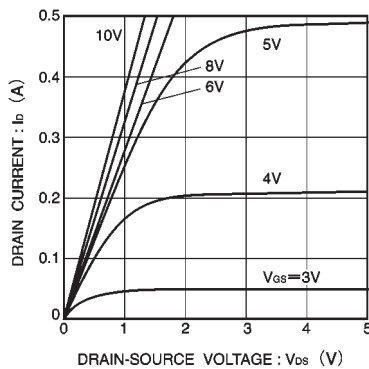
**Typical Characteristics**


Fig.1 Typical output characteristics

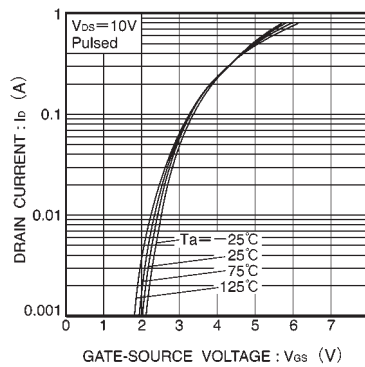


Fig.2 Typical transfer characteristics

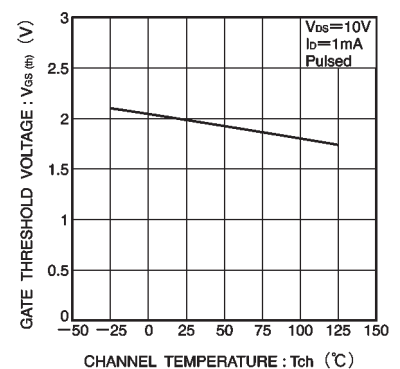


Fig.3 Gate threshold voltage vs. channel temperature

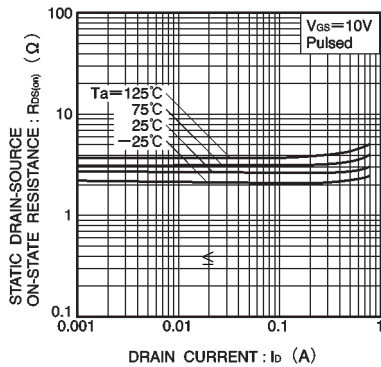


Fig.4 Static drain-source on-state resistance vs. drain current ( I )

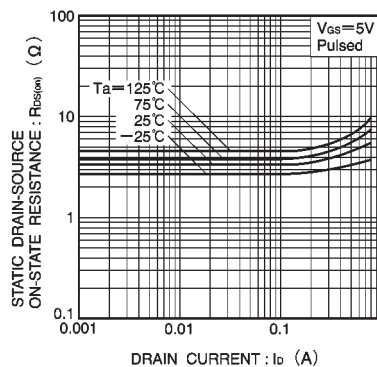


Fig.5 Static drain-source on-state resistance vs. drain current ( II )

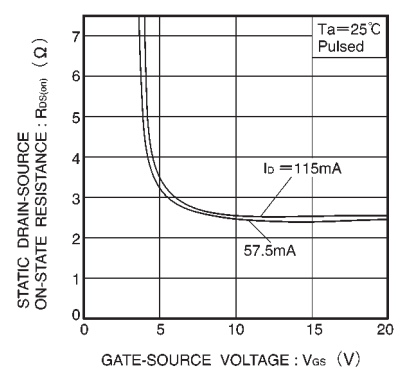


Fig.6 Static drain-source on-state resistance vs. gate-source voltage

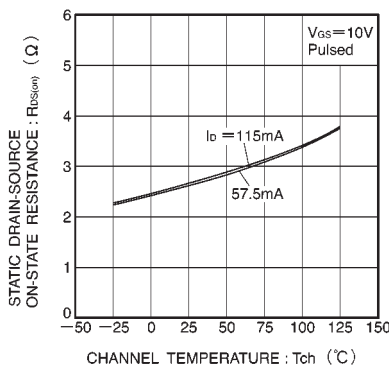


Fig.7 Static drain-source on-state resistance vs. channel temperature

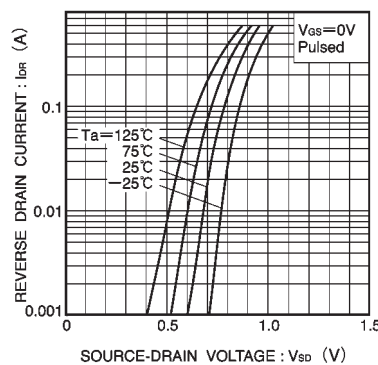


Fig.8 Reverse drain current vs. source-drain voltage ( I )

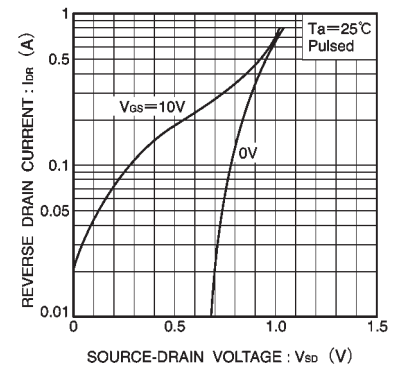


Fig.9 Reverse drain current vs. source-drain voltage ( II )

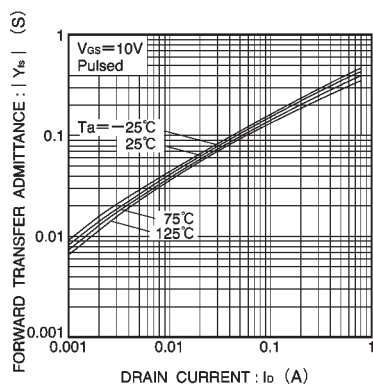


Fig.10 Forward transfer admittance vs. drain current

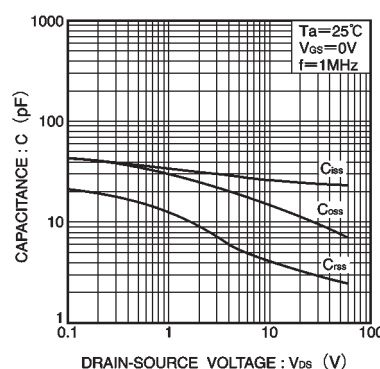


Fig.11 Typical capacitance vs. drain-source voltage

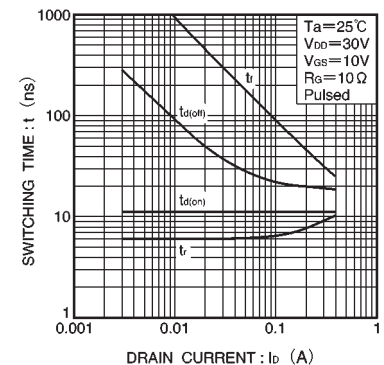
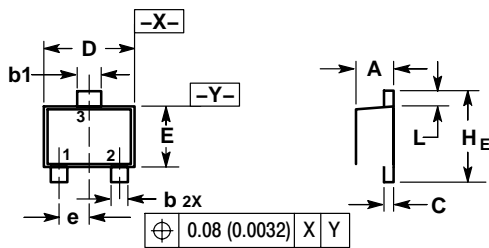


Fig.12 Switching characteristics (See Figures 13 and 14 for the measurement circuit and resultant waveforms)

Packaging: SOT-723

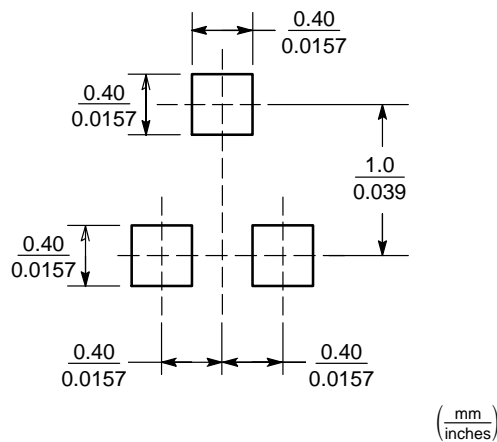


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
b	0.15	0.20	0.27	0.0059	0.0079	0.0106
b1	0.25	0.3	0.35	0.010	0.012	0.014
C	0.07	0.12	0.17	0.0028	0.0047	0.0067
D	1.15	1.20	1.25	0.045	0.047	0.049
E	0.75	0.80	0.85	0.03	0.032	0.034
e	0.40 BSC			0.016 BSC		
H E	1.15	1.20	1.25	0.045	0.047	0.049
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

**SOLDERING FOOTPRINT**





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